



# STPS30150CT/CW/CFP

## HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

### MAIN PRODUCT CHARACTERISTICS

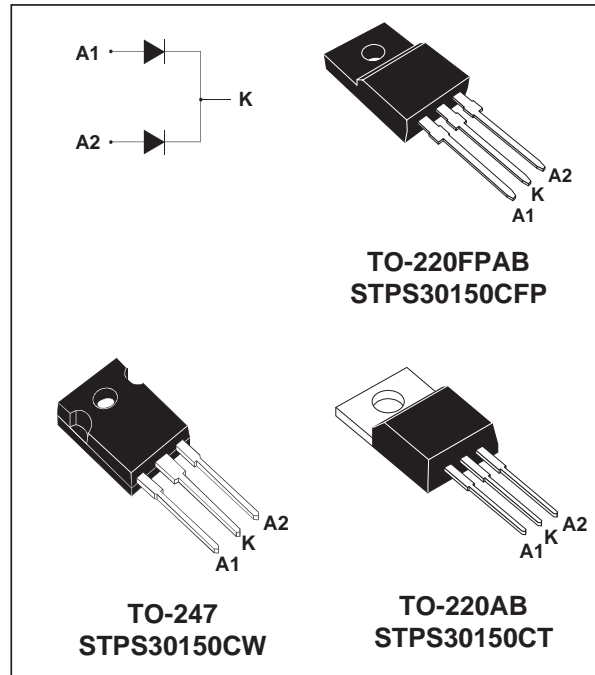
$I_{F(AV)}$	2 x 15 A
$V_{RRM}$	150 V
$T_j$	175°C
$V_F(max)$	0.75 V

### FEATURES AND BENEFITS

- High junction temperature capability
- Good trade off between leakage current and forward voltage drop
- Low leakage current
- Insulated Package: TO-220FPAB  
Insulating voltage: 2000V DC  
Capacitance: 45pF

### DESCRIPTION

Dual center tap schottky rectifier designed for high frequency Switched Mode Power Supplies.



### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage			150	V	
$I_{F(RMS)}$	RMS forward current			30	A	
$I_{F(AV)}$	Average forward current $\delta = 0.5$	TO-220FPAB	$T_c = 110^\circ\text{C}$	per diode per device	15	A
		TO-220AB	$T_c = 155^\circ\text{C}$			
		TO-247		30		
$I_{FSM}$	Surge non repetitive forward current		$t_p = 10 \text{ ms}$ sinusoidal	220	A	
$T_{stg}$	Storage temperature range			- 65 to + 175	°C	
$T_j$	Maximum operating junction temperature *			175	°C	
$dV/dt$	Critical rate of rise of reverse voltage			10000	V/ $\mu\text{s}$	

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink

**THERMAL RESISTANCES**

Symbol	Parameter		Value	Unit
R <sub>th(j-c)</sub>	Junction to case	TO-220FPAB	Per diode Total	4 3.3
		TO-220AB	Per diode Total	1.6 0.85
		TO-247	Per diode Total	1.5 0.8
R <sub>th(c)</sub>		TO-220FPAB	Coupling	2.6
		TO-220AB	Coupling	0.1
		TO-247	Coupling	0.1

When the diodes 1 and 2 are used simultaneously :  
 $\Delta T_{j(\text{diode } 1)} = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$

**STATIC ELECTRICAL CHARACTERISTICS (per diode)**

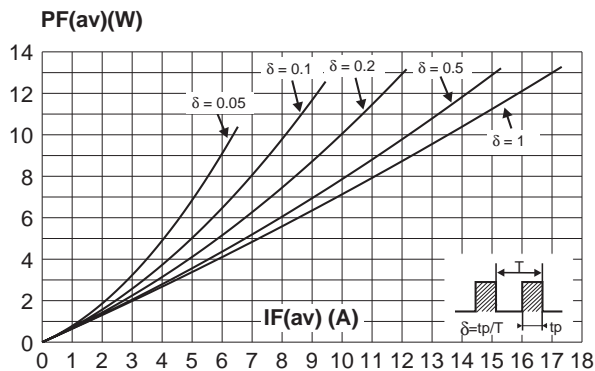
Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> *	Reverse leakage current	T <sub>j</sub> = 25°C	V <sub>R</sub> = V <sub>RRM</sub>			6.5	μA
		T <sub>j</sub> = 125°C				8	mA
V <sub>F</sub> **	Forward voltage drop	T <sub>j</sub> = 25°C	I <sub>F</sub> = 15 A			0.92	V
		T <sub>j</sub> = 125°C	I <sub>F</sub> = 15 A		0.69	0.75	
		T <sub>j</sub> = 25°C	I <sub>F</sub> = 30 A			1	
		T <sub>j</sub> = 125°C	I <sub>F</sub> = 30 A		0.8	0.86	

Pulse test : \* tp = 5 ms, δ < 2%  
 \*\* tp = 380 μs, δ < 2%

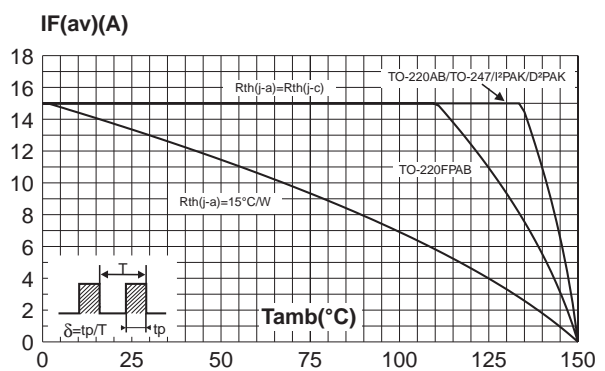
To evaluate the conduction losses use the following equation:

$$P = 0.64 \times I_{F(AV)} + 0.0073 I_{F(RMS)}^2$$

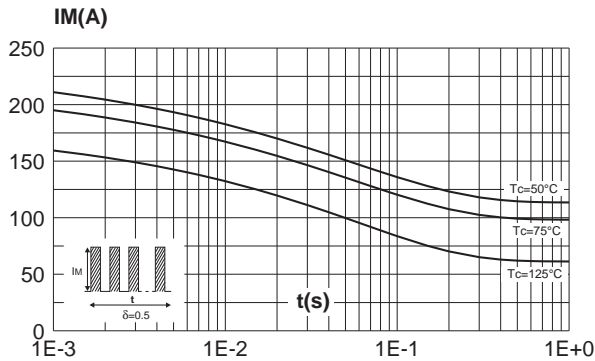
**Fig. 1:** Average forward power dissipation versus average forward current (per diode).



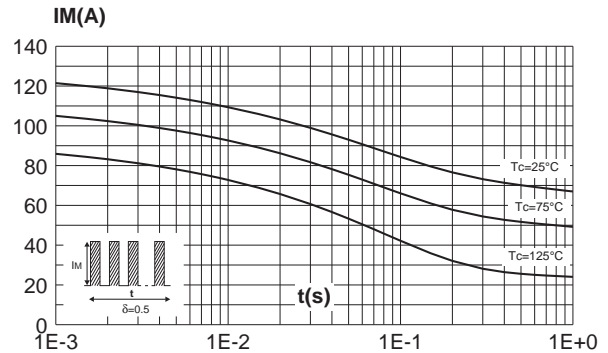
**Fig. 2:** Average forward current versus ambient temperature (δ = 0.5, per diode).



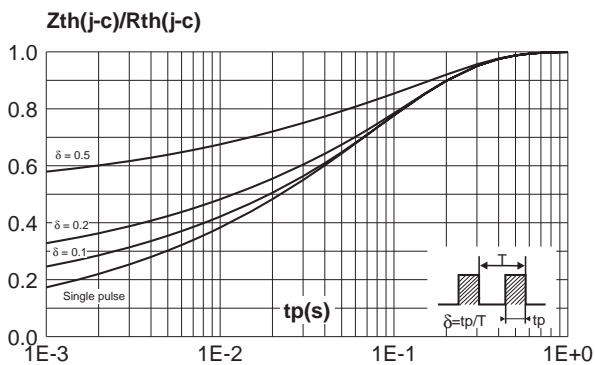
**Fig. 3-1:** Non repetitive surge peak forward current versus overload duration (maximum values, per diode).



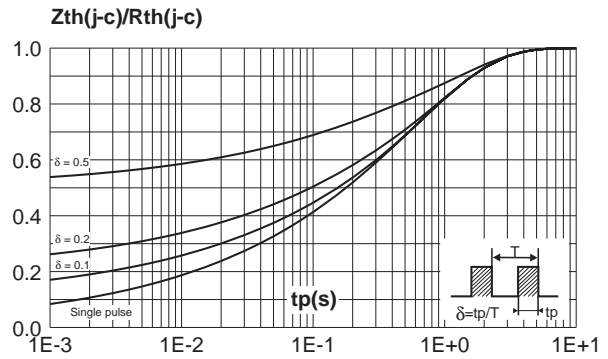
**Fig. 3-2:** Non repetitive surge peak forward current versus overload duration (maximum values, per diode) (TO-220FPAB only).



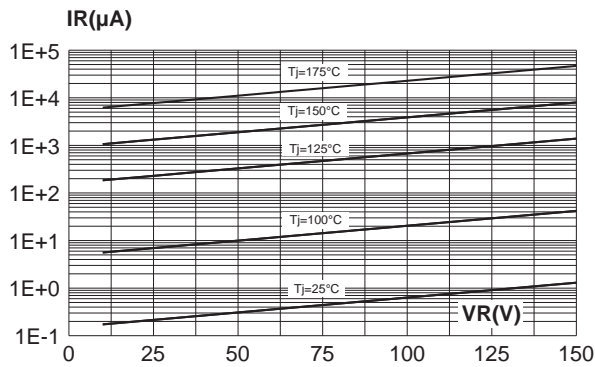
**Fig. 4-1:** Relative variation of thermal impedance junction to case versus pulse duration (per diode)



**Fig. 4-2:** Relative variation of thermal impedance junction to case versus pulse duration. (TO-220FPAB)



**Fig. 5:** Reverse leakage current versus reverse voltage applied (typical values, per diode).



**Fig. 6:** Junction capacitance versus reverse voltage applied (typical values, per diode).

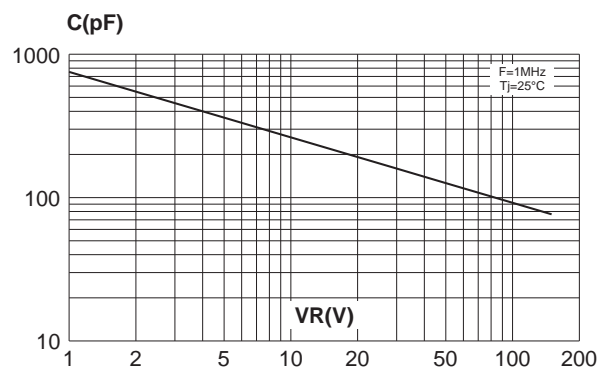
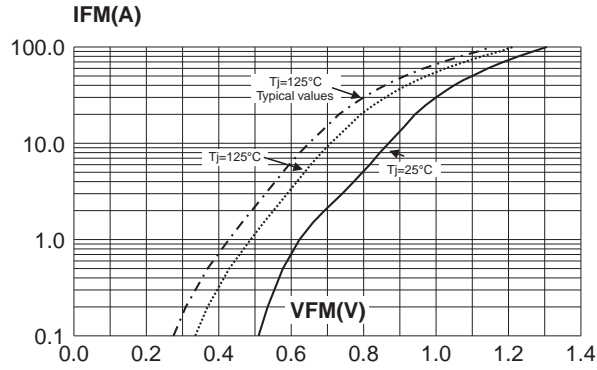
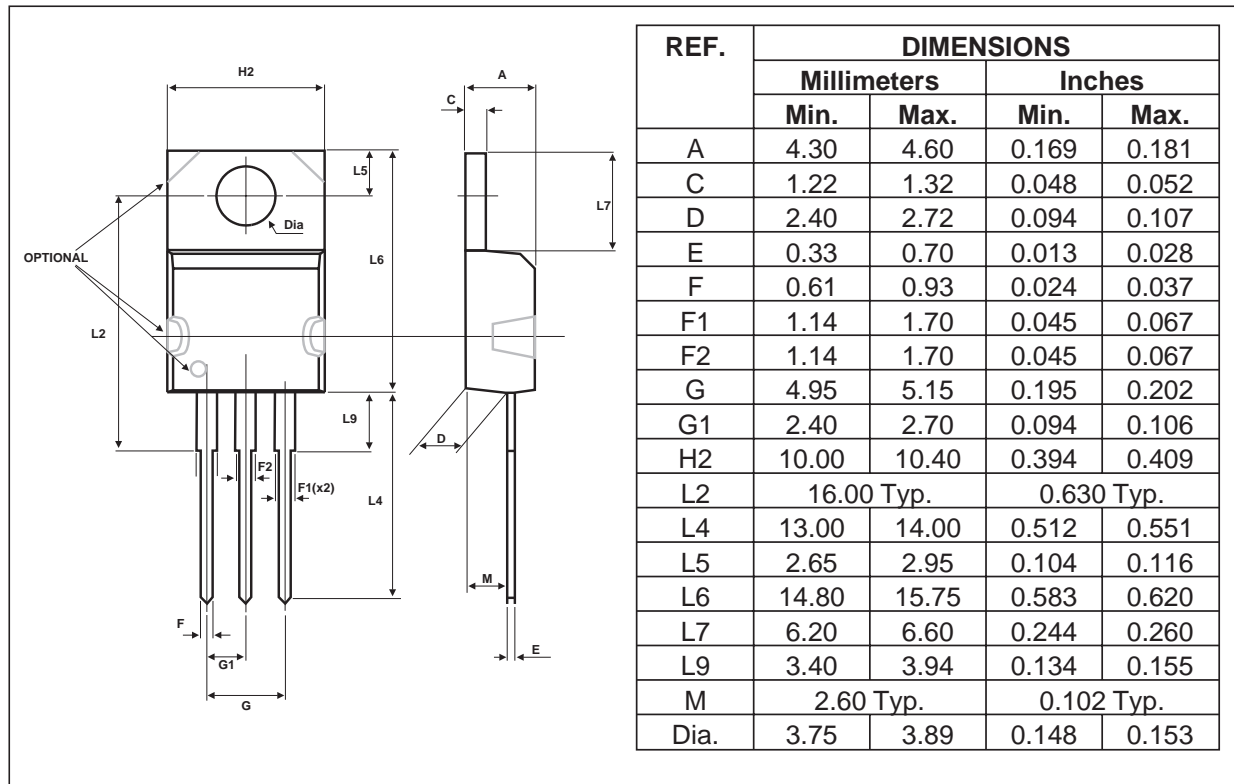


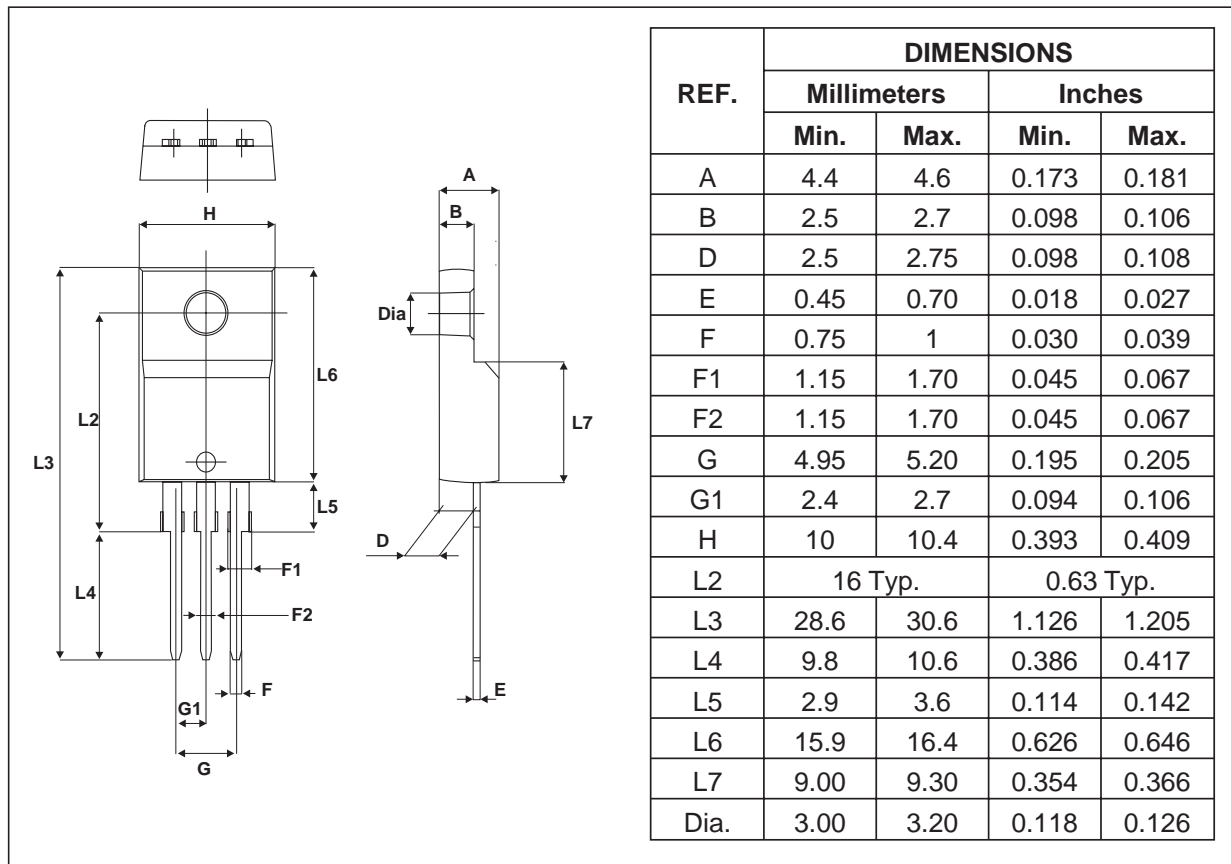
Fig. 7: Forward voltage drop versus forward current (maximum values, per diode).



PACKAGE MECHANICAL DATA  
TO-220AB

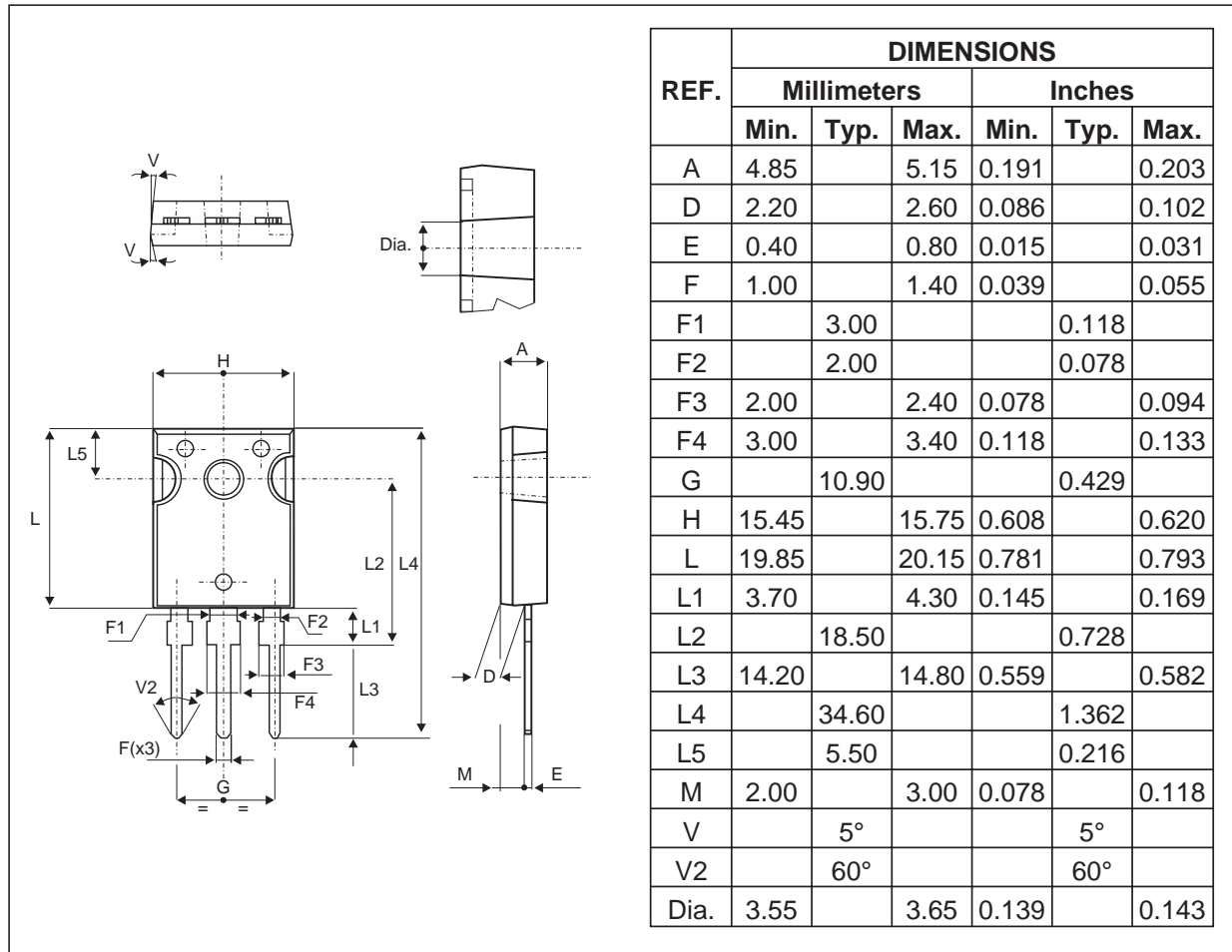


**PACKAGE MECHANICAL DATA**  
TO-220FPAB



**STPS30150CT/CW/CFP**

**PACKAGE MECHANICAL DATA**  
TO-247



- Cooling method : C
- Recommended torque value : 0.8m.N
- Maximum torque value : 1.0m.N

Ordering Type	Marking	Package	Weight	Base qty	Delivery mode
STPS30150CT	STPS30150CT	TO-220AB	2 g	50	Tube
STPS30150CFP	STPS30150CFP	TO-220FPAB	1.9 g	50	Tube
STPS30150CW	STPS30150CW	TO-247	4.4 g	30	Tube

- Epoxy meets UL94, V0

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